Notification about the transfer of the semiconductor business

The semiconductor business of Panasonic Corporation was transferred on September 1, 2020 to Nuvoton Technology Corporation (hereinafter referred to as "Nuvoton"). Accordingly, Panasonic Semiconductor Solutions Co., Ltd. became under the umbrella of the Nuvoton Group, with the new name of Nuvoton Technology Corporation Japan (hereinafter referred to as "NTCJ").

In accordance with this transfer, semiconductor products will be handled as NTCJ-made products after September 1, 2020. However, such products will be continuously sold through Panasonic Corporation.

Publisher of this Document is NTCJ.

If you would find description "Panasonic" or "Panasonic semiconductor solutions", please replace it with NTCJ.

* Except below description page

"Request for your special attention and precautions in using the technical information and semiconductors described in this book"

Nuvoton Technology Corporation Japan



Silicon N-channel MOSFET

SK8603180L

MOS FET SK8603180L

For Load-switching / For DC-DC Converter

- Features
- Low Drain-source On-state Resistance : RDS(on) typ = 6.7 mΩ (VGS = 4.5 V)
- Halogen-free / RoHS compliant (EU RoHS / UL-94 V-0 / MSL : Level 1 compliant)
- Marking Symbol :18
- Packaging

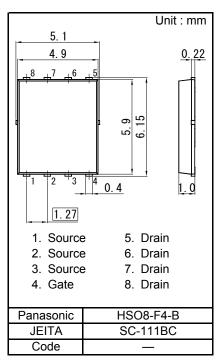
Embossed type (Thermo-compression sealing): 3 000 pcs / reel (standard)

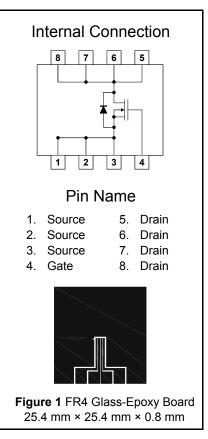
Absolute Maximum Ratings Ta = 25 °C								
Parameter			Symbol	Rating	Unit			
Drain to Source Voltage			VDS	30	V			
Gate to Source Voltage			VGS	±20	v			
	Ta = 25 °C, t = 10 s ^{*1}		ID	20				
Drain Current	Ta = 25 °C, DC ^{*1}			15	А			
	Tc = 25 °C			39	A			
	Pulsed	l, Tch < 150 °C ^{*2}		60				
Total Power		Ta = 25 °C, DC ^{*1}	PD	2.4	W			
Dissipation		Tc = 25 °C	FD	19	٧V			
Thermal Resistance		Channel to Ambient	Rth(ch-a)	51	°C/W			
	ance	Channel to Case	Rth(ch-c)	6.6	C/W			
Channel Temperature			Tch	150				
Operating ambient temperature			Topr	-40 to +85	°C			
Storage Temperature Range			Tstg	-55 to +150				
Avalanche Current (Single pulse) *3			IAR	10	А			
Avalanche Energy (Single pulse) *3			EAR	12	mJ			

Note *1 Device mounted on a glass-epoxy board in Figure 1

*2 Pulse test: Ensure that the channel temperature does not exceed 150 °C

*3 VDD = 24 V, VGS = 10 to 0 V, L = 0.1 mH, Tch = 25 $^{\circ}$ C (initial)





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■ Electrical Characteristics Ta = 25 °C ± 3 °C

Static Characteristics

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Drain-source Breakdown Voltage	VDSS	ID = 1 mA, VGS = 0 V	30			V
Zero Gate Voltage Drain Current	IDSS	VDS = 30 V, VGS = 0 V			10	μA
Gate-source Leakage Current	IGSS	VGS = ±16 V, VDS = 0 V			±10	μA
Gate-source Threshold Voltage	Vth	ID = 1.45 mA, VDS = 10 V	1.3		3	V
Drain-source On-state Resistance	. ,	ID = 10 A, VGS = 10 V		5.1	7.1	mΩ
	RDS(on)2	ID = 10 A, VGS = 4.5 V		6.7	9.8	

Dynamic Characteristics

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Input Capacitance	Ciss	VDS = 10 V, VGS = 0 V		1 200	1 680	
Output Capacitance	Coss	f = 1 MHz		140	196	pF
Reverse Transfer Capacitance	Crss			100	160	
Turn-on Delay Time ^{*1}	td(on)	VDD = 15 V, VGS = 0 to 10 V ID = 10 A		8		ns
Rise Time ^{*1}	tr			6		
Turn-off Delay Time ^{*1}	td(off)	VDD = 15 V, VGS = 10 to 0 V ID = 10 A		39		ns
Fall Time ^{*1}	tf			6		
Total Gate Charge	Qg			9.2		
Gate to Source Charge	Qgs	VDD = 15 V, VGS = 0 to 4.5 V ID = 10 A		3		nC
Gate to Drain Charge	Qgd			3.5		
Gate resistance	rg	f = 5 MHz		1.4	3	Ω

Body Diode Characteristic

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Diode Forward Voltage	VSD	IS = 10 A, VGS = 0 V		0.8	1.2	V

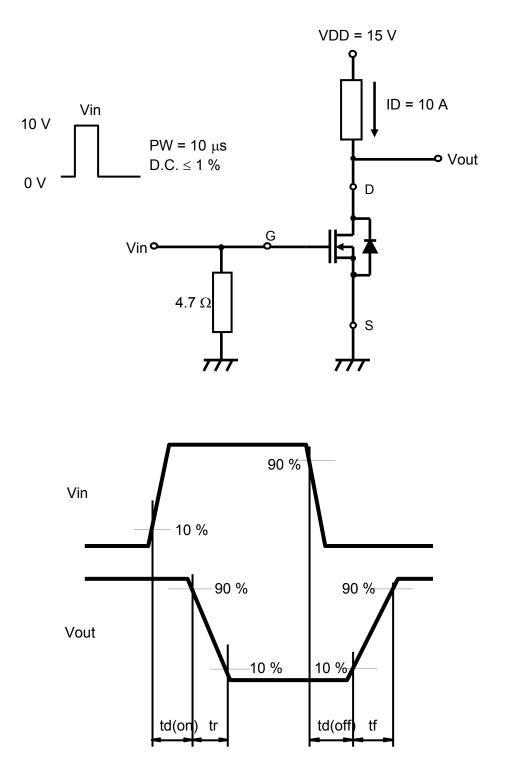
Note: 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 Measuring methods for transistors.

2. *1 Measurement circuit for Turn-on Delay Time / Rise Time / Turn-off Delay Time / Fall Time

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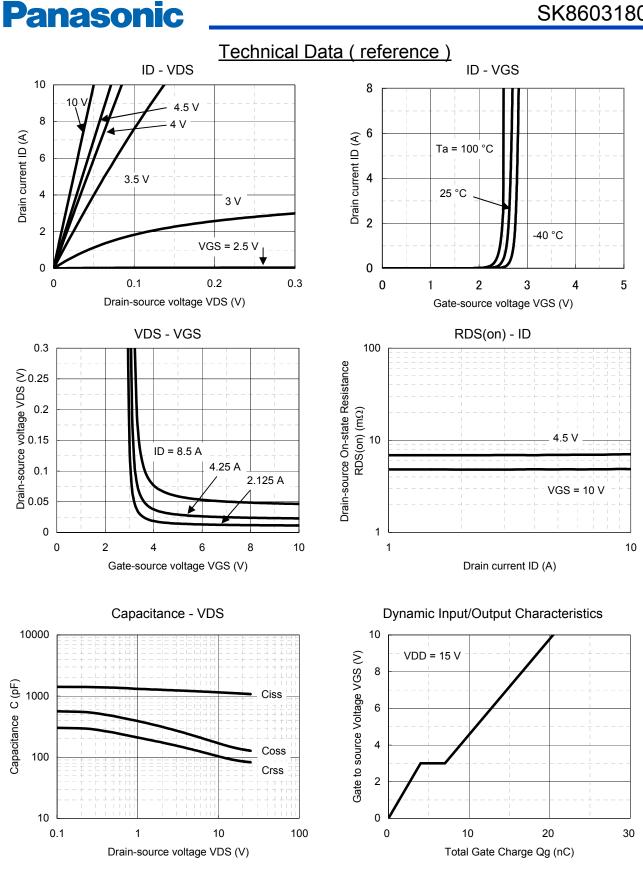


*1 Measurement circuit for Turn-on Delay Time / Rise Time / Turn-off Delay Time / Fall Time



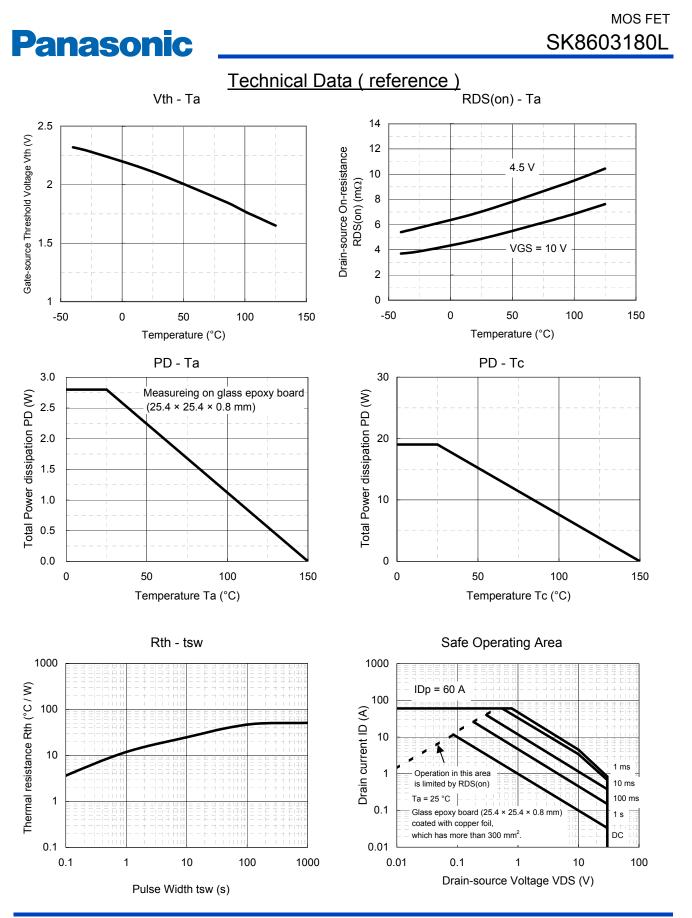
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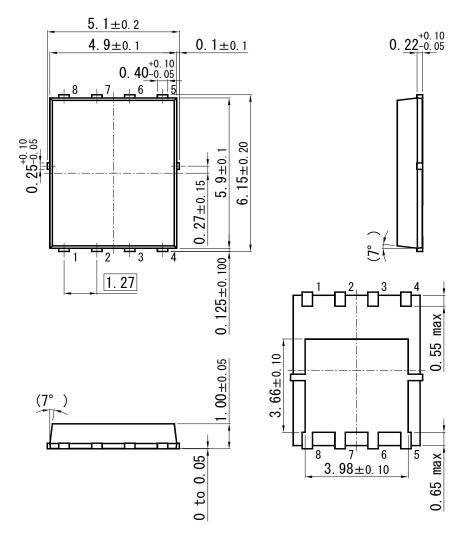
Established : 2012-09-26 Revised : 2013-05-31



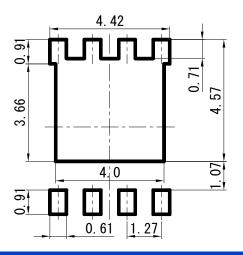


MOS FET SK8603180L

HSO8-F4-B



Land Pattern (Reference) (Unit : mm)



Established : 2012-09-26 Revised : 2013-05-31

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